

Efficient tight-binding Monte Carlo structural sampling of complex materials

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While recent work towards the development of tight-binding and ab-initio algorithms has focused on molecular dynamics, Monte Carlo methods can often lead to better results with relatively little effort. We present here a multi-step Monte Carlo algorithm that makes use of the possibility of quickly evaluating local energies. For the thermalization of a 1000-atom configuration of α -Si, this algorithm gains about an order of magnitude in speed over standard molecular dynamics. The algorithm can easily be ported to a wide range of materials and can be dynamically optimized for a maximum efficiency.

Monte Carlo techniques are extensively used in statistical physics, but have received relatively little attention in the materials theory community. Most of the recent efforts towards the development of fast tight-binding or ab-initio codes, for example, has been done within the framework of molecular dynamics (MD) [1–3]. Since all atoms move simultaneously within MD, there are limitations to the approaches that can be used. In particular, the most promising order-N MD-based methods [4–6] are only applicable to materials with a well-defined electronic gap, reducing significantly the number of problems that can be studied with such algorithms. Monte Carlo (MC) techniques, on the other hand, allow a much wider range of steps to be used and provide an alternative to MD for a number of problems.

In this Letter, we introduce such a Monte Carlo algorithm. For a 1000-atom tight-binding model, we find a gain in efficiency of an order of magnitude over MD without the need for a perfectly clean electronic gap or any other special consideration. We first describe the core of the algorithm and then present some of the details associated with computing the intermediate steps. Examples are given using a series of amorphous silicon models described by the tight-binding interaction of Kwon *et al.* [7].

The general problem that we address here is the generation of a set of configurations, defined by the atomic positions $\vec{X} \equiv \{\vec{x}_1, \dots, \vec{x}_N\}$, sampled according to the microcanonical ensemble, i.e., with a probability proportional to their Boltzmann weight:

$$P(\vec{X}) \sim \exp(-\beta E(\vec{X})), \quad (1)$$

where $E(\vec{X})$ is the total potential energy of configuration $\vec{X}$ and $\beta = (k_b T)^{-1}$, the inverse of Boltzmann's constant k_b times the temperature T . This sampling can be done using standard MD or MC.

In Monte Carlo, a markovian chain of configurations is generated through a sequence of trial moves or elementary steps. A standard move is obtained by randomly displacing a configuration $\vec{X}_i$ to a trial position $\vec{X}'_{i+1} = \vec{X}_i + \delta\vec{X}$, shifting one or all atoms in the box. The trial move is then accepted with a probability given by the Metropolis criterion [8]

$$P_a = \text{Min}[1, \exp(-\beta \delta E)]. \quad (2)$$

where $\delta E = E(\vec{X}'_{i+1}) - E(\vec{X}_i)$ is the energy difference between the trial and the initial positions.

A straightforward implementation of this standard Monte Carlo algorithm requires thus one full energy calculation per trial step, making it usually much slower than a standard MD simulation. It is possible, however, to speed up the MC simulation significantly, especially as the cost of computing the total energy increases faster than linear with the system size. This improvement exploits the fact that the energy difference between two configurations, δE , which differ only locally, can be estimated in a much quicker way than the total energy, as discussed below. Using this approximate value, the acceptance ratio, Eq. 2, is modified as follows:

$$P_a = \text{Min} \left[1, \exp \left(-\tilde{\beta} \delta \tilde{E} \right) \right] \times \text{Min} \left[1, \exp \left(-\beta \delta E + \tilde{\beta} \delta \tilde{E} \right) \right], \quad (3)$$

where $\tilde{\beta}$ is an inverse temperature close to β . Note that detailed balance is still strictly obeyed, irrespectively of the quality of the estimate and the value of $\tilde{\beta}$. This expression can be implemented by first using an accept-reject procedure based on the first factor, followed by an accept-reject procedure based on the second factor *only*

if the first one is accepted. The gain in doing this is that the first factor in this equation requires only an *estimate* of the energy difference, which is easily computed, while the second factor, that involves an expensive total energy calculation, is computed *only* if the first one is accepted. If the estimate is accurate, $\tilde{\beta}$ can be chosen equal to β and the acceptance probability for the second factor is close to unity; effectively a full energy calculation is only required per *accepted* step rather than per *trial* step. Since rejected moves are now cheaper, the trial step size can be enlarged for an increased efficiency.

A further reduction in the number of full energy calculations is possible by making a sequence of M intermediate displacement steps, each one accepted or rejected based on the estimate of the energy difference, followed by a single accept-reject procedure which requires a full energy calculation. The resulting acceptance ratio, which still strictly preserves detailed balance, becomes

$$P_a = \prod_{i=1}^M \left[\text{Min} \left[1, \exp \left(-\tilde{\beta} \delta \tilde{E}_i \right) \right] \right] \times \text{Min} \left[1, \exp \left(-\beta \delta E - \sum_{i=1}^M \tilde{\beta} \delta \tilde{E} \right) \right]. \quad (4)$$

These two variables, the number and typical size of the intermediate trial moves M , can then be optimized for speed. For large simulation cells, a good choice is to select a trial step size yielding a local acceptance ratio around 50%, and to maximize the number of intermediate (cheap) trial moves M under the constraint that the global acceptance ratio does not fall below 50%. The resulting M depends on the accuracy of the energy estimates.

Depending on the system (i.e., metal or insulator, crystalline, disordered solid, or liquid), there are different types of Monte Carlo moves for which approximate energy differences can be computed efficiently and accurately. In metals, for example, a MC move localized in real space can be combined with an embedded-atom potential, while a MC move localized in reciprocal space is more appropriate in conjunction with plane-waves *ab-initio* calculations. Here, we present an approach designed for semiconductors and insulators, and apply it to models of amorphous silicon described by the tight-binding interaction developed by Goodwin, Skinner and Pettifor [9] and modified by Kwon *et al.* [7].

Within the tight-binding formalism, the total energy can be written as

$$E = \sum_i \langle \Psi_i | H | \Psi_i \rangle + E_r + E_0 N_a \quad (5)$$

where the first term represents the electronic contribution of the energy given by the sum of the occupied eigenvalues of the tight-binding Hamiltonian H , the second term represents the ion-ion repulsion as well as the correction

from the double counting of the electron-electron interaction and E_0 is a constant energy shift per atom, and N_a is the total number of atoms in the system. Details of the potential and parameters used here can be found in Ref. [7].

We want to compute the approximate energy differences between two systems that are close to each other. Because amorphous silicon is a semiconductor, we keep the difference between the two configurations localized in real space. Consider two configurations A and B with total energies E_A and E_B respectively, such that the atomic coordinates differ only in a small region around a point $\vec{x}_m$; for instance, in a Monte Carlo approach with single-atom displacements, it is convenient to select $\vec{x}_m = (\vec{x}_i + \vec{x}'_i)/2$, the geometrical center between the “active” region before and after the displacement [10]. A spherical localization volume is constructed around $\vec{x}_m$, large enough to include the displaced atoms or atoms and its local environment, following the *principle of near-sightedness* of an equilibrium system [11] which asserts that the effects on the deformation on atoms outside the localization volume is small. As discussed below, for the model system used here, a sphere including about a hundred atoms around $\vec{x}_m$ is found to be sufficient.

This discussion may be written formally. Denoting I and II as the regions inside and outside the localization volume, the exact energy difference can be written as

$$\begin{aligned} \delta E_{AB} &= E_B - E_A \\ &= (E_B^I + E_B^{II}) - (E_A^I + E_A^{II}) \\ &= (E_B^I - E_A^I) + (E_B^{II} - E_A^{II}). \end{aligned}$$

To obtain an estimate of the approximate energy difference, we assume that the contribution from region II for both configurations is the same. This is a good approximation as long as the radius of the localized volume is greater than the localization length of the density matrix of the system. The approximate energy difference $\delta \tilde{E}_{AB}$ is therefore simply given by $\delta \tilde{E}_{AB} = E_B^I - E_A^I$. Furthermore, if the localization volume is big enough and remains stationary during the atomic movement, the boundary effects too can be neglected. We construct a local Hamiltonian for the localization region I before and after the movement with open boundary condition and calculate the band energies for the corresponding local Hamiltonian, the difference of which would give us the approximate change of the band energy in the two configurations. Typically in our calculations we have used volumes with a radius of 7.5 Å, which roughly corresponds to a hundred atoms.

We emphasize that although the quality of the approximation is strongly related to the degree of localization, the algorithm works even if there are states in the gap. In this case, the error in the estimate increases but will be corrected for appropriately in the final MC step using the full energy calculation. In this sense, the algorithm

is much more stable under the presence of defects than a typical order- N MD.

We test this scheme on three sample configurations of α -Si with 300, 500 and 1000 atoms, respectively. The initial cells were prepared using the optimized Wooten-Winer-Weaire [12] bond-switching algorithm described in Ref. [13]. This method, which uses a Keating interaction potential [14], produces the best α -Si models to date, from a structural and electronic point of view.

First, we establish the validity of our approximate calculation of the energy difference between two nearby configurations. As shown in Fig. 1, where we compare the approximate energy, $\delta\tilde{E}_{AB}$, with the exact energy difference obtained by direct diagonalization of the full cell, the error implicit in this approximation is about 0.03 eV, sufficiently small for the following simulations. The exact value of the error depends, of course, on a number of variables: the distance between the original and the modified configuration, the size of the localization volume, and the local strain (which might delocalize some electronic states). The error appears, however, independent of the size of the simulation cell, which is to be expected because of the aforementioned principle of nearsightedness. For the results plotted in Fig. 1, we selected a Monte Carlo step of 0.4 Å, much larger than the value we used in our Monte Carlo simulations.

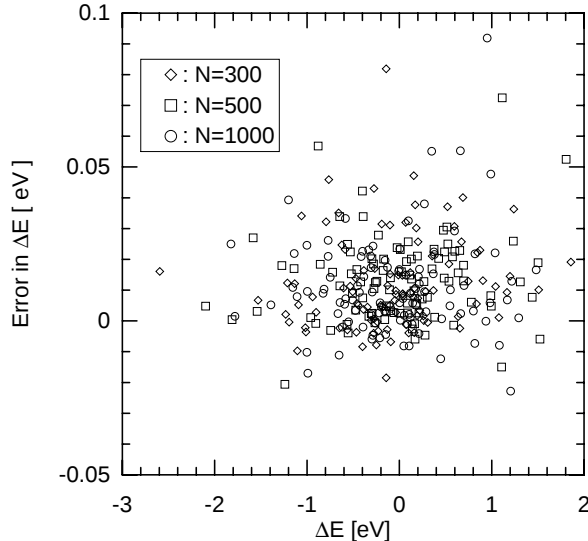


FIG. 1. Accuracy of the $O(1)$ estimate of the energy difference between two similar configurations as described in the text. The exact energy difference δE between two configurations, calculated using a direct diagonalization method, is plotted horizontally. The difference between the exact and estimated energy differences is plotted vertically. The different symbols stand for the system sizes indicated in the figure.

The efficiency of the various methods is determined by how fast each samples the phase space. One way to measure this, is to estimate the thermalization time from a configuration which is out of equilibrium. Starting from

the three configurations described above, which are optimized for the Keating potential at zero K, we relax the atomic positions at 300 K using two MC algorithms and an MD run. In the first MC approach, dubbed the standard MC approach, a trial configuration $\tilde{X}'_{i+1}$ is obtained from the old configuration $\tilde{X}_i$ by adding a gaussian random number to each of the $3N$ degrees of freedom. The change in total energy $\delta E = E(\tilde{X}'_{i+1}) - E(\tilde{X}_i)$ is calculated, requiring a full total energy computation. Next, the trial configuration is either accepted or rejected following a Metropolis probability as described in Eq. (2). The spread of the gaussian distribution is chosen so to maximize the diffusion in phase space. For our simulations with $N = 300$ atoms, the atomic step size is 0.01 Å; it decreases with increasing system size to about 0.0025 Å for a 1000-atom simulation.

The second method approach, called the multi-local approach, is the Monte Carlo scheme proposed here: multiple local displacements, accepted or rejected based on an estimate of the energy difference, followed by a single full total energy calculation to recover correct sampling of the Boltzmann distribution. Here, the size M of the sequence of local moves and the size of the atomic displacements are chosen so to maximize the diffusion in phase space; the values we used are $M = 300$ and a step size of 0.1 Å.

The standard MD simulation is performed at constant temperature, by rescaling the velocities at every time step. This modifies the trajectory but ensures a faster convergence than a more flexible constraint dynamics, damping considerably the thermal oscillations. In MD, the forces also need to be computed, in addition to the total energy. This requires the evaluation of the eigenvectors of the tight-binding Hamiltonian, a step which is not necessary in MC, and which increases the computational cost as well as the memory requirements significantly. In spite of these additional costs, MD is much faster than standard MC, since it is a second-order scheme which makes use of inertia.

We compare the computational efficiency of these methods in figure 2, which shows the evolution of the total energy as a function of CPU time on a fast workstation (DEC Alpha, 21264 architecture, 667 MHz) for the methods applied to three different size cells. All curves are fitted to the function

$$E(t) - E(0) = a(1 - \exp(-t/\tau) \cos(\omega t - \phi)). \quad (6)$$

Here, the initial excess energy is given by a , the thermalization time by τ , and the oscillatory behavior in MD by ω and ϕ ; in the fits to the MC data, we took $\omega = \phi = 0$ since MC inherently does not show oscillatory behavior. Important for us are the thermalization times. The fitted parameters for the multi-local MC approach are $\tau/N^3 = 21, 8.0$ and $6.2 \mu\text{s}$, respectively, for system sizes $N=300, 500$ and 1000 atoms. For MD, we find

$\tau/N^3 = 32, 35$ and $49 \mu\text{s}$, respectively. (The increase in τ/N^3 for MD is probably due to the cache misses.) Clearly, the multi-local MC outperforms MD with an increasing factor as a function of system size; it is close to an order of magnitude faster for the 1000-atom cell.

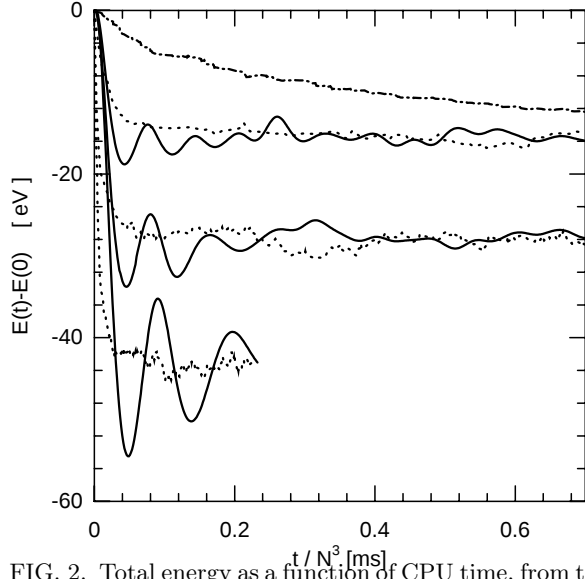


FIG. 2. Total energy as a function of CPU time, from top to bottom for system sizes $N = 300, 500$ and 1000 . The dashed curves correspond to results obtained with the non-local MC approach, the solid lines are obtained with molecular dynamics. For the 300-atom model, the total energy with the standard MC approach is plotted as the dash-dotted line.

The total self-diffusion $\sum_i [\vec{r}_i(t) - \vec{r}_i(0)]^2$ corresponding to these runs is reported in Fig. 3. The MD curves show oscillatory behavior due to inertia, while the overdamped MC dynamics leads to smooth non-decreasing diffusion. The sudden jumps at irregular intervals are caused by activated events. The difference in the displacement at the end of the simulations tells that MC and MD have not reached the same local basin.

The resulting atomic configurations show excellent structural and electronic properties; for the largest sample, the angular spread is 10.6 degrees (with a nearest-neighbor cut-off anywhere between $2.7 \text{ \AA}$ and $2.9 \text{ \AA}$), and the band gap is clean. A detailed study of the structural and electronic properties is in progress [15].

Besides its higher efficiency, the MC approach is also more flexible. It can easily concentrate the computational effort on the activate parts of a heterogeneous system, for instance, an interfacial area in a heterostructure, or the hydrogen atoms in $\alpha\text{-Si:H}$. Furthermore, the efficiency can be raised by allowing well-chosen complex moves that involve more than single-atom displacements. In the case of $\alpha\text{-Si}$, for example, we could include bond transpositions that dominate the low-temperature dynamics [16].

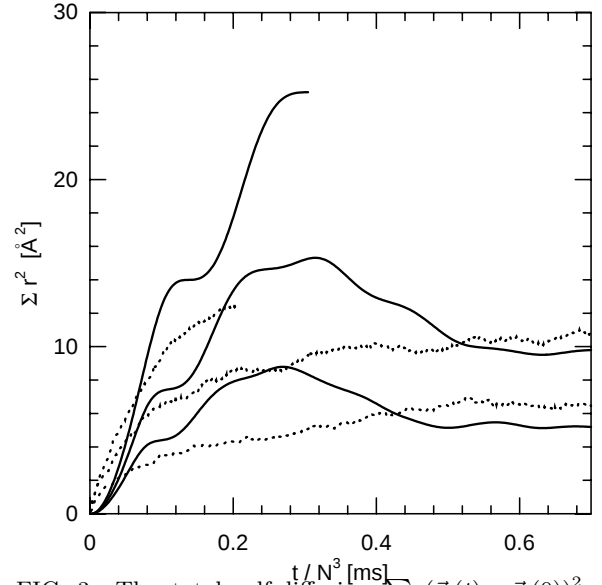


FIG. 3. The total self-diffusion $\sum_i (\vec{r}_i(t) - \vec{r}_i(0))^2$ as a function of CPU time, for system sizes $N = 300$ (bottom), $N = 500$ (middle) and $N = 1000$ (top). The solid curves correspond to MD and the dashed lines to the multi-local MC.

In summary, we have presented here a multi-local Monte Carlo procedure that exploits the fact that good estimations of energy differences between relatively close configurations can often be obtained cheaply. This permits us to construct a two-stage algorithm which first accepts-rejects a large number of moves based on this approximate calculation of the energy and then corrects the accumulated errors with a final accept-reject step using one full energy computation. This method is highly flexible and can easily be adapted to a wide-range of problems including those for which order- N molecular dynamics is inapplicable.

We have also presented an implementation of this algorithm for thermalization of tight-binding $\alpha\text{-Si}$ models. In this case, the multi-local MC outperforms MD in the exploration of phase space by up to an order of magnitude.

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- [1] E. Kim and Y.H Lee, Phys. Rev. B **49**, 1743 (1994)
 - [2] L. Colombo, Annual Reviews of Computational Physics, Vol. 4 (edited by D. Stauffer, World Scientific, Singapore, 1996)
 - [3] S. Goedecker and M. Teter, Phys. Rev. B **51**, 9455 (1995)
 - [4] P. Ordejon, D.A. Drabold, R.M.Martin and M.P. Grumbach, Phys. Rev. B **51**, 1456 (1995); U. Stephen and D.A.

- Drabold, Phys. Rev. B **57**, 6391 (1998)
- [5] X.-P. Li, R.W. Nunes and D. Vanderbilt, Phys. Rev. B **47**, 10891 (1993); R.W. Nunes and D. Vanderbilt, Phys. Rev. B **50**, 17611 (1994)
 - [6] S. Goedecker, Reviews of Mod. Phys. **71**, 1085 (1999)
 - [7] I. Kwon, R. Biswas, C.Z. Wang, K.M. Ho, and C.M. Soukoulis, Phys. Rev. B **49**, 7242 (1994)
 - [8] N. Metropolis, A.W. Rosenbluth, M.N. Rosenbluth, A.H. Teller, and E. Teller, J. Chem. Phys. **21**, 1087 (1953).
 - [9] L. Goodwin, A.J. Skinner and D.G. Pettifor, Europhys. Lett. **9**, 701-706 (1989).
 - [10] One aspect that is important for the proof of correctness of the Monte Carlo approach is that the localization region is centered around $\vec{x}_m$, thus independent whether the starting point was A or B , i.e., $\delta\tilde{E}_{AB} = -\delta\tilde{E}_{BA}$. If for instance the localization region would have been centered around A , this property would not hold any longer, and detailed balance would be violated.
 - [11] W. Kohn, Phys. Rev. Lett. **76**, 17 (1996); V. Heine in *Solid State Physics*, Vol. **35** (Academic Press).
 - [12] F. Wooten, K. Winer and D. Weaire, Phys. Rev. Lett. **54**, 1392 (1985); F. Wooten and D. Weaire, Solid State Physics **40**, 1 (1987).
 - [13] G.T. Barkema and N. Mousseau, Phys. Rev. B **62**, 4985-4990 (2000).
 - [14] P. N. Keating, Phys. Rev. **145**, 637 (1966).
 - [15] P. Biswas, to be published.
 - [16] G.T. Barkema and N. Mousseau, Phys. Rev. Lett. **81**, 1865 (1998); N. Mousseau and G.T. Barkema, Phys. Rev. B **61**, 1898 (2000).